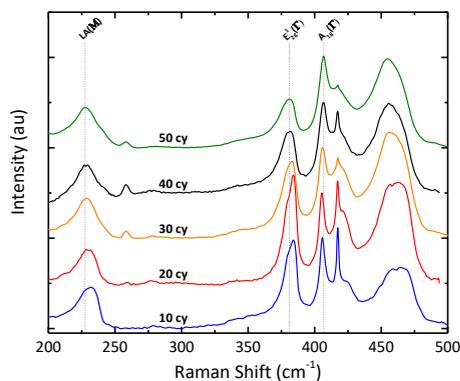
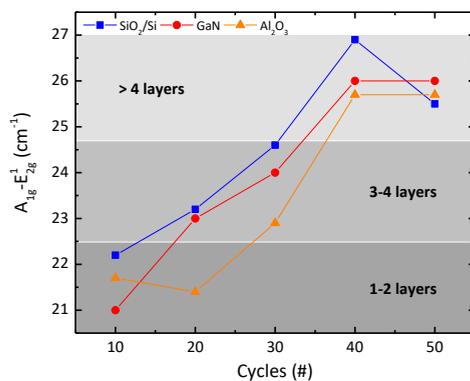


Effect of Substrate on MoS₂ Deposited by Plasma-enhanced Atomic Layer Deposition

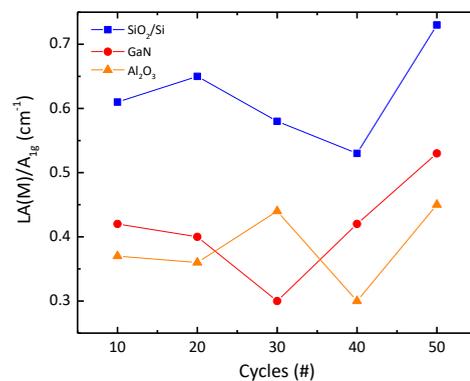
Asad J. Mughal, Timothy N. Walter, Kayla A. Cooley, Adam Bertuch, and Suzanne E. Mohney



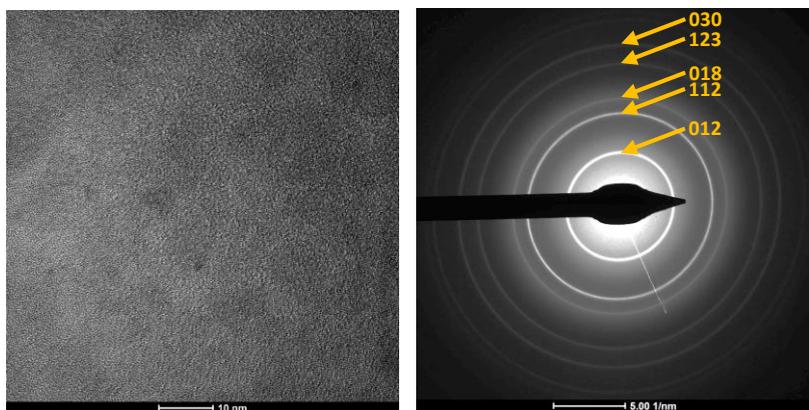
Resonance Raman spectra of PEALD MoS₂ at different deposition cycles indicating a shift in vibrational modes with decreasing film thickness.



Difference between A_{1g} and E_{1g} is indicative of layer thickness.

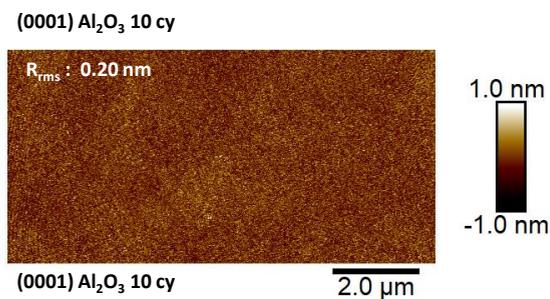


Ratio between LA(M) and A_{1g} (LA(M)/A_{1g}) has an inverse correlation to grain size.



Plan-view TEM and SAED of MoS₂ deposited on a transparent SiN_x membrane

- SAED indexed to 2H-MoS₂
- Systematic absence of (00 l) shows that the basal plane of MoS₂ is parallel to the surface
- Polycrystalline



AFM micrograph of MoS₂ film grown on (0001) sapphire for 10 reaction cycles. The film is smooth with no evidence for out-of-plane growth.